# Switch-mode Power Rectifier 45 V, 30 A

#### **Features and Benefits**

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 30 A Total (15 A Per Diode Leg)
- Guard-Ring for Stress Protection

#### **Applications**

- Power Supply Output Rectification
- Power Management
- Instrumentation

#### **Mechanical Characteristics:**

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 50 Units Per Plastic Tube
- This is a Pb-Free Device\*

#### **MAXIMUM RATINGS**

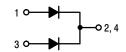
Please See the Table on the Following Page



#### ON Semiconductor®

www.onsemi.com

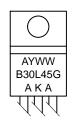
# DUAL SCHOTTKY BARRIER RECTIFIERS 30 AMPERES, 45 VOLTS



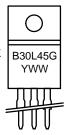
#### MARKING DIAGRAMS



TO-220 CASE 221A PLASTIC







B30L45 = Device Code A = Assembly Location Y = Year

Y = Year

WW = Work Week

AKA = Polarity Designator

G = Pb-Free Device

#### **ORDERING INFORMATION**

Device	Package	Shipping
MBR30L45CTG	TO-220 (Pb-Free)	50 Units/Rail
MBRF30L45CTG	TO-220FP (Pb-Free)	50 Units/Rail

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### MAXIMUM RATINGS (Per Diode Leg)

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	45	V
Average Rectified Forward Current (Rated $V_R$ ) $T_C = 137^{\circ}C$		I <sub>F(AV)</sub>	15	Α
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz)		I <sub>FRM</sub>	30	Α
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)			190	Α
Operating Junction Temperature (Note 1)		TJ	-55 to +150	°C
Storage Temperature		T <sub>stg</sub>	- 55 to +175	°C
Voltage Rate of Change (Rated V <sub>R</sub> )		dv/dt	10,000	V/μs
ESD Ratings: Machine Model = C Human Body Model = 3B			> 400 > 8000	V
HERMAL CHARACTERISTICS			•	
Maximum Thermal Resistance (MBR30L45CTG) (MBRF30L45CTG)	Junction-to-Case Junction-to-Ambient Junction-to-Case	R <sub>θJC</sub> R <sub>θJA</sub> R <sub>θJC</sub>	1.9 45 2.2	°C/W
LECTRICAL CHARACTERISTICS (Per Diode Leg)				
Maximum Instantaneous Forward Voltage (Note 2) $ \begin{aligned} &(I_F=15 \text{ A, } T_C=25^\circ\text{C})\\ &(I_F=15 \text{ A, } T_C=125^\circ\text{C})\\ &(I_F=30 \text{ A, } T_C=25^\circ\text{C})\\ &(I_F=30 \text{ A, } T_C=125^\circ\text{C}) \end{aligned} $		VF	0.50 0.44 0.61 0.60	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^{\circ}C$ ) (Rated DC Voltage, $T_C = 125^{\circ}C$ )		i <sub>R</sub>	0.65 250	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

The heat generated must be less than the thermal conductivity from Junction–to–Ambient: dP<sub>D</sub>/dT<sub>J</sub> < 1/R<sub>θJA</sub>.
 Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2.0%.

#### **TYPICAL CHARACTERISTICS**

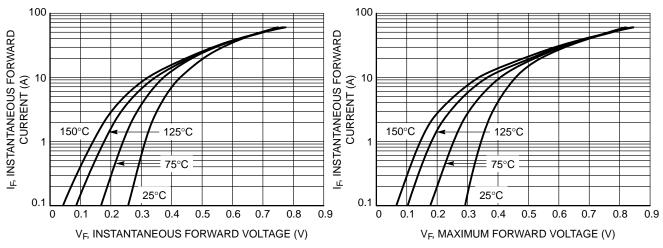
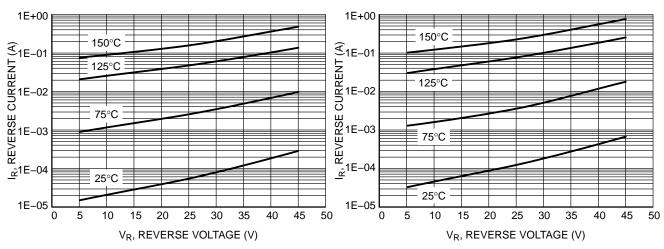


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage



**Figure 3. Typical Reverse Current** 

**Figure 4. Maximum Reverse Current** 

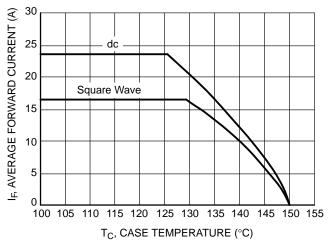


Figure 5. Current Derating

#### **TYPICAL CHARACTERISTICS**

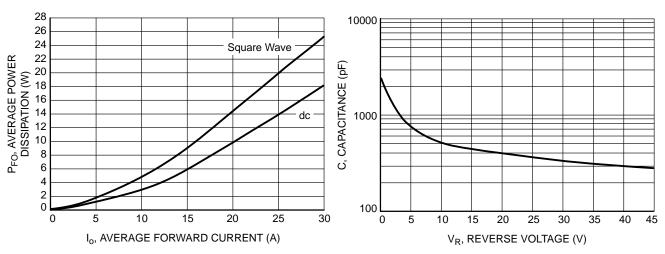


Figure 6. Forward Power Dissipation

Figure 7. Typical Capacitance

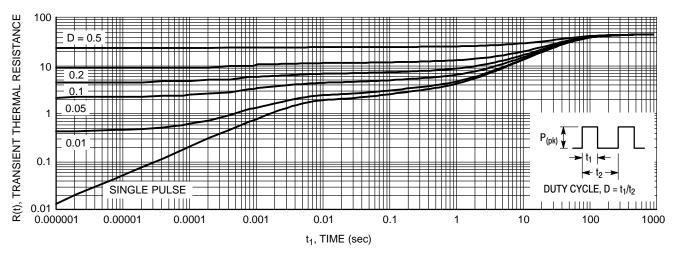


Figure 8. Thermal Response Junction-to-Ambient for MBR30L45CTG

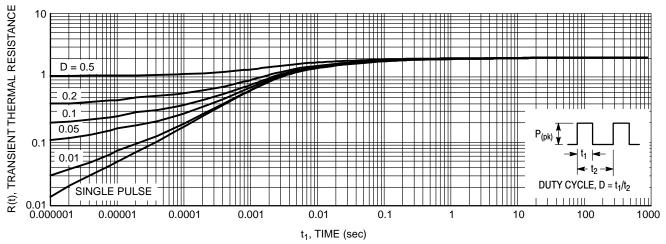


Figure 9. Thermal Response Junction-to-Case for MBR30L45CTG

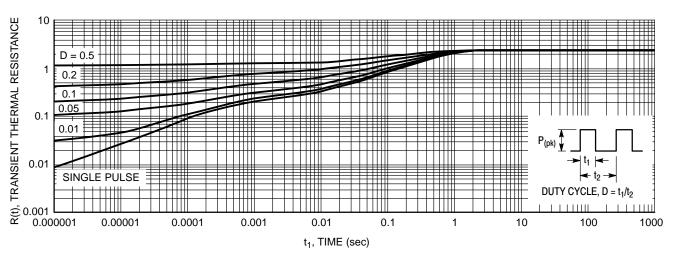
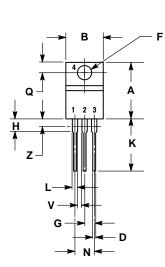
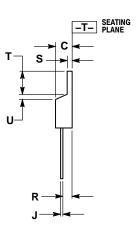


Figure 10. Thermal Response Junction-to-Case for MBRF30L45CTG

#### **PACKAGE DIMENSIONS**

TO-220 CASE 221A-09 **ISSUE AH** 





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

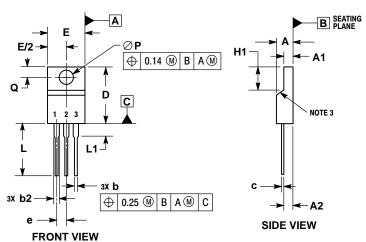
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

- STYLE 6:
  PIN 1. ANODE
  2. CATHODE
  3. ANODE
  4. CATHODE

#### PACKAGE DIMENSIONS

#### TO-220 FULLPACK, 3-LEAD

CASE 221AH ISSUE F

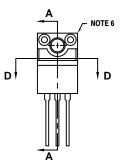


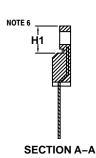
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- . CONTROLLING DIMENSION: MILLIMETERS. CONTOUR UNCONTROLLED IN THIS AREA.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
- DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY
- MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS AT AND H1 FOR MANUFACTURING PURPOSES.

		MILLIMETERS		
L	DIM	MIN	MAX	
	Α	4.30	4.70	
	A1	2.50	2.90	
	A2	2.50	2.90	
	b	0.54	0.84	
	b2	1.10	1.40	
	С	0.49	0.79	
	D	14.70	15.30	
	Е	9.70	10.30	
	е	2.54 BSC		
	H1	6.60	7.10	
L	L	12.50	14.73	
	L1		2.80	
	Р	3.00	3.40	
	Q	2.80	3.20	







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